# **74AUP2G07**

# Low-power dual buffer with open-drain output

Rev. 8 — 17 September 2015

**Product data sheet** 

## 1. General description

The 74AUP2G07 provides two non-inverting buffers with open-drain output. The output of the device is an open drain and can be connected to other open-drain outputs to implement active-LOW wired-OR or active-HIGH wired-AND functions.

Schmitt-trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

#### 2. Features and benefits

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
  - ◆ JESD8-12 (0.8 V to 1.3 V)
  - ◆ JESD8-11 (0.9 V to 1.65 V)
  - ◆ JESD8-7 (1.2 V to 1.95 V)
  - ◆ JESD8-5 (1.8 V to 2.7 V)
  - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
  - ♦ HBM JESD22-A114F Class 3A exceeds 5000 V
  - ◆ MM JESD22-A115-A exceeds 200 V
  - ◆ CDM JESD22-C101E exceeds 1000 V
- Low static-power consumption;  $I_{CC} = 0.9 \mu A$  (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V<sub>CC</sub>
- I<sub>OFF</sub> circuitry provides partial power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



## Low-power dual buffer with open-drain output

# 3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AUP2G07GW	-40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363
74AUP2G07GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1.45 $\times$ 0.5 mm	SOT886
74AUP2G07GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1 $\times$ 0.5 mm	SOT891
74AUP2G07GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115
74AUP2G07GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 1.0 $\times$ 1.0 $\times$ 0.35 mm	SOT1202
74AUP2G07GX	–40 °C to +125 °C	X2SON6	plastic thermal extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 0.8 $\times$ 0.35 mm	SOT1255

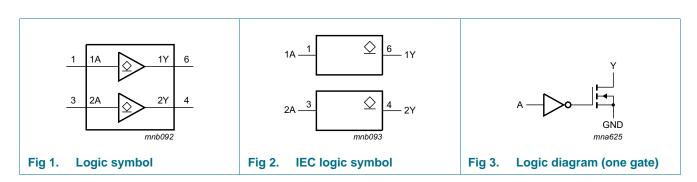
# 4. Marking

#### Table 2. Marking

Type number	Marking code <sup>[1]</sup>
74AUP2G07GW	р7
74AUP2G07GM	р7
74AUP2G07GF	р7
74AUP2G07GN	р7
74AUP2G07GS	р7
74AUP2G07GX	р7

<sup>[1]</sup> The pin 1 indicator is located on the lower left corner of the device, below the marking code.

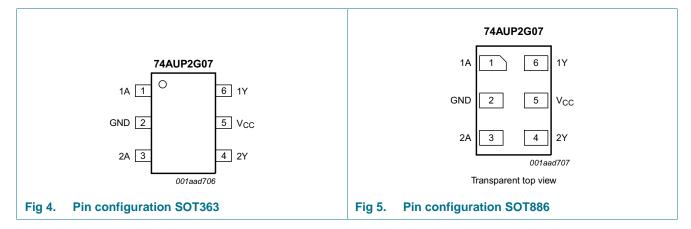
# 5. Functional diagram



## Low-power dual buffer with open-drain output

# 6. Pinning information

## 6.1 Pinning





## 6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1A	1	data input
GND	2	ground (0 V)
2A	3	data input
2Y	4	data output
V <sub>CC</sub>	5	supply voltage
1Y	6	data output

#### Low-power dual buffer with open-drain output

# 7. Functional description

Table 4. Function table[1]

Input	Output
nA	nY
L	L
Н	Z

<sup>[1]</sup> H = HIGH voltage level; L = LOW voltage level; Z = high-impedance OFF state.

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+4.6	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V	-50	-	mA
VI	input voltage	[1]	-0.5	+4.6	V
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode [1]	-0.5	+4.6	V
Io	output current	$V_O = 0 \text{ V to } V_{CC}$	-	20	mA
I <sub>CC</sub>	supply current		-	50	mA
I <sub>GND</sub>	ground current		-50	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } +125  ^{\circ}\text{C}$ [2]	-	250	mW

<sup>[1]</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

# 9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		8.0	3.6	V
V <sub>I</sub>	input voltage		0	3.6	V
Vo	output voltage	Active mode and Power-down mode	0	3.6	V
T <sub>amb</sub>	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V <sub>CC</sub> = 0.8 V to 3.6 V	0	200	ns/V

<sup>[2]</sup> For SC-88 package: above 87.5  $^{\circ}$ C the value of P<sub>tot</sub> derates linearly with 4.0 mW/K. For X2SON6 and XSON6 packages: above 118  $^{\circ}$ C the value of P<sub>tot</sub> derates linearly with 7.8 mW/K.

### Low-power dual buffer with open-drain output

# 10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = 2	5 °C					
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 0.8 V	$0.70 \times V_{CC}$	-	-	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.6	-	-	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 0.8 V	-	-	$0.30 \times V_{CC}$	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	-	0.9	V
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_{O}$ = 20 $\mu$ A; $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	$0.3 \times V_{CC}$	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.31	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.31	V
		$I_{O}$ = 2.3 mA; $V_{CC}$ = 2.3 V	-	-	0.31	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.44	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
I <sub>I</sub>	input leakage current	$V_I$ = GND to 3.6 V; $V_{CC}$ = 0 V to 3.6 V	-	-	±0.1	μΑ
l <sub>OZ</sub>	OFF-state output current	$V_I = V_{IH}$ ; $V_O = 0 \ V$ to 3.6 V; $V_{CC} = 0 \ V$ to 3.6 V	-	-	±0.1	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_{I}$ or $V_{O} = 0 \text{ V}$ to 3.6 V; $V_{CC} = 0 \text{ V}$	-	-	±0.2	μА
$\Delta I_{OFF}$	additional power-off leakage current	$V_{I}$ or $V_{O} = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.2	μΑ
I <sub>CC</sub>	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μΑ
$\Delta I_{CC}$	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	40	μΑ
Cı	input capacitance	$V_{CC} = 0 \text{ V to } 3.6 \text{ V; } V_{I} = \text{GND or } V_{CC}$	-	0.7	-	pF
Co	output capacitance	$V_O = GND; V_{CC} = 0 V$	-	0.9	-	pF
T <sub>amb</sub> = -	40 °C to +85 °C	-				1
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 0.8 V	$0.70 \times V_{CC}$	-	-	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	0.65 × V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.6	-	-	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 0.8 V	-	-	0.30 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	-	-	0.35 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	-	0.9	V

### Low-power dual buffer with open-drain output

**Table 7. Static characteristics** ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_{O} = 20 \mu A$ ; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	$0.3 \times V_{CC}$	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.37	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.35	V
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.45	V
		$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	V
l <sub>l</sub>	input leakage current	$V_I$ = GND to 3.6 V; $V_{CC}$ = 0 V to 3.6 V	-	-	±0.5	μΑ
l <sub>OZ</sub>	OFF-state output current	$V_I = V_{IH}$ ; $V_O = 0 \text{ V to } 3.6 \text{ V}$ ; $V_{CC} = 0 \text{ V}$ to 3.6 V	-	-	±0.5	μА
I <sub>OFF</sub>	power-off leakage current	$V_I$ or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.5	μΑ
$\Delta I_{OFF}$	additional power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V to 0.2 V	-	-	±0.6	μА
I <sub>CC</sub>	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μА
$\Delta I_{CC}$	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	50	μΑ
T <sub>amb</sub> = -	40 °C to +125 °C					
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 0.8 V	$0.75 \times V_{CC}$	-	-	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	$0.70 \times V_{CC}$	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.6	-	-	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.0	-	-	V
$V_{IL}$	LOW-level input voltage	V <sub>CC</sub> = 0.8 V	-	-	$0.25 \times V_{CC}$	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	-	-	$0.30 \times V_{CC}$	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	-	0.9	V
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_{O}$ = 20 $\mu$ A; $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.11	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	$0.33 \times V_{CC}$	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.41	V
		$I_{O} = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.39	V
		$I_{O}$ = 2.3 mA; $V_{CC}$ = 2.3 V	-	-	0.36	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
l <sub>l</sub>	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.75	μΑ
l <sub>OZ</sub>	OFF-state output current	$V_{I} = V_{IH}$ ; $V_{O} = 0 \text{ V to } 3.6 \text{ V}$ ; $V_{CC} = 0 \text{ V}$ to 3.6 V	-	-	±0.75	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_1$ or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.75	μΑ

### Low-power dual buffer with open-drain output

 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$\Delta I_{OFF}$	additional power-off leakage current	$V_1$ or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μΑ
I <sub>CC</sub>	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μΑ
$\Delta I_{CC}$	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	75	μΑ

# 11. Dynamic characteristics

#### Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C <sub>L</sub> = 5 p	F			·					
t <sub>pd</sub>	propagation delay	nA to nY; see Figure 8							
		V <sub>CC</sub> = 0.8 V	-	11.6	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	2.1	4.1	7.5	1.7	9.1	10.0	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	1.6	3.0	5.1	1.3	6.1	6.7	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	1.6	2.7	4.0	1.2	5.0	5.5	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.1	2.1	3.2	0.9	4.0	4.4	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	1.4	2.2	2.8	1.1	3.3	3.6	ns
C <sub>L</sub> = 10	pF							'	
t <sub>pd</sub>	propagation delay	nA to nY; see Figure 8							
		V <sub>CC</sub> = 0.8 V	-	14.7	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	3.0	5.1	9.0	2.4	11.2	12.3	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	2.3	3.8	6.1	2.0	7.4	8.1	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	2.4	3.6	4.8	1.8	6.1	6.7	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.7	2.8	3.8	1.3	4.8	5.3	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.2	3.1	4.2	1.6	4.5	5.0	ns
C <sub>L</sub> = 15	pF					1		1	
t <sub>pd</sub>	propagation delay	nA to nY; see Figure 8							T
		V <sub>CC</sub> = 0.8 V	-	17.7	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	3.5	6.1	10.4	3.2	13.1	14.5	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	3.0	4.5	6.8	2.6	8.6	9.4	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	2.8	4.4	6.7	2.2	7.8	8.6	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	2.4	3.4	4.5	1.9	5.3	5.8	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.2	4.0	5.7	1.9	6.1	6.7	ns

## Low-power dual buffer with open-drain output

 Table 8.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	_
C <sub>L</sub> = 30	pF								
t <sub>pd</sub>	propagation delay	nA to nY; see Figure 8 [2]							
		V <sub>CC</sub> = 0.8 V	-	26.7	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	4.8	9.0	15.6	4.3	18.8	20.7	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	4.1	6.7	9.4	3.7	11.8	13.0	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	3.8	6.8	9.7	3.2	11.0	12.1	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	3.7	5.2	6.7	3.0	7.1	7.8	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	3.6	6.4	9.7	2.8	10.4	11.4	ns
$C_L = 5 p$	F, 10 pF, 15 pF and	30 pF						'	
C <sub>PD</sub>	power dissipation	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$ [3][4]							
	capacitance	V <sub>CC</sub> = 0.8 V	-	0.5	-	-	-	-	pF
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	0.6	-	-	-	-	pF
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	0.6	-	-	-	-	pF
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	0.7	-	-	-	-	pF
l		V <sub>CC</sub> = 2.3 V to 2.7 V	-	0.9	-	-	-	-	pF
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	1.2	-	-	-	-	pF

<sup>[1]</sup> All typical values are measured at nominal V<sub>CC</sub>.

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N$$
 where:

 $f_i$  = input frequency in MHz;

V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching.

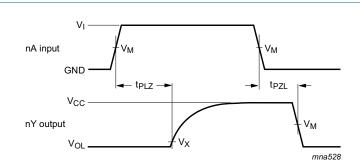
<sup>[2]</sup>  $\;\;t_{pd}$  is the same as  $t_{PZL}$  and  $t_{PLZ}.$ 

<sup>[3]</sup> All specified values are the average typical values over all stated loads.

<sup>[4]</sup>  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

#### Low-power dual buffer with open-drain output

#### 12. Waveforms



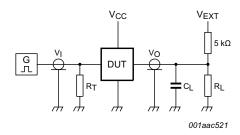
Measurement points are given in Table 9.

Logic level:  $V_{OL}$  is the typical output voltage level that occurs with the output load.

Fig 8. The data input (nA) to output (nY) propagation delays

Table 9. Measurement points

Supply voltage	Input	Output		
V <sub>cc</sub>	V <sub>M</sub>	V <sub>M</sub>	V <sub>X</sub>	
0.8 V to 1.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V <sub>OL</sub> + 0.1 V	
1.65 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V <sub>OL</sub> + 0.15 V	
3.0 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V <sub>OL</sub> + 0.3 V	



Test data is given in Table 10.

Definitions for test circuit:

R<sub>L</sub> = Load resistance.

C<sub>L</sub> = Load capacitance including jig and probe capacitance.

 $R_T$  = Termination resistance should be equal to the output impedance  $Z_0$  of the pulse generator.

 $V_{\mathsf{EXT}}$  = External voltage for measuring switching times.

Fig 9. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Input		Load		V <sub>EXT</sub>		
V <sub>CC</sub>	VI	t <sub>r</sub> , t <sub>f</sub>	CL	R <sub>L</sub> [1]	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	$t_{PZL}, t_{PLZ}$
0.8 V to 3.6 V	V <sub>CC</sub>	≤ 3 ns	5 pF, 10 pF, 15 pF and 30 pF	$5$ k $\Omega$ or $1$ M $\Omega$	open	GND	$2 \times V_{CC}$

<sup>[1]</sup> For measuring enable and disable times  $R_L$  = 5 k $\Omega$ , for measuring propagation delays, set-up and hold times and pulse width  $R_L$  = 1 M $\Omega$ .

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# 13. Package outline

# **SOT363** Plastic surface-mounted package; 6 leads Α X = v M A ⊕ w M B detail X scale **DIMENSIONS (mm are the original dimensions)** Α1 UNIT Α D Q Ε ٧ $H_{\mathsf{E}}$ $L_{\mathbf{p}}$ у max 0.25 0.10 0.25 0.30 2.2 1.8 1.35 1.15 0.45 1.1 0.8 0.20 0.15 0.15

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT363			SC-88			<del>-04-11-08-</del> 06-03-16	

Fig 10. Package outline SOT363 (SC-88)

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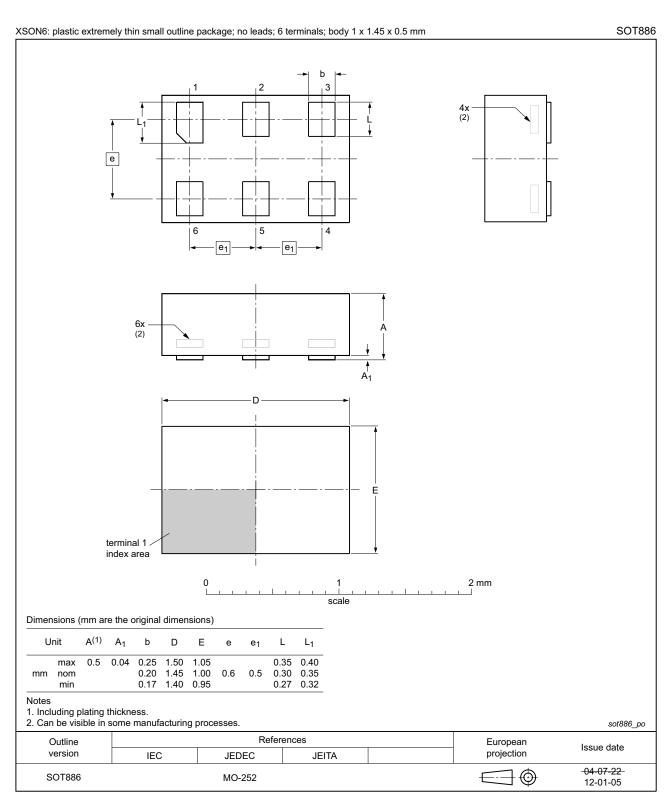


Fig 11. Package outline SOT886 (XSON6)

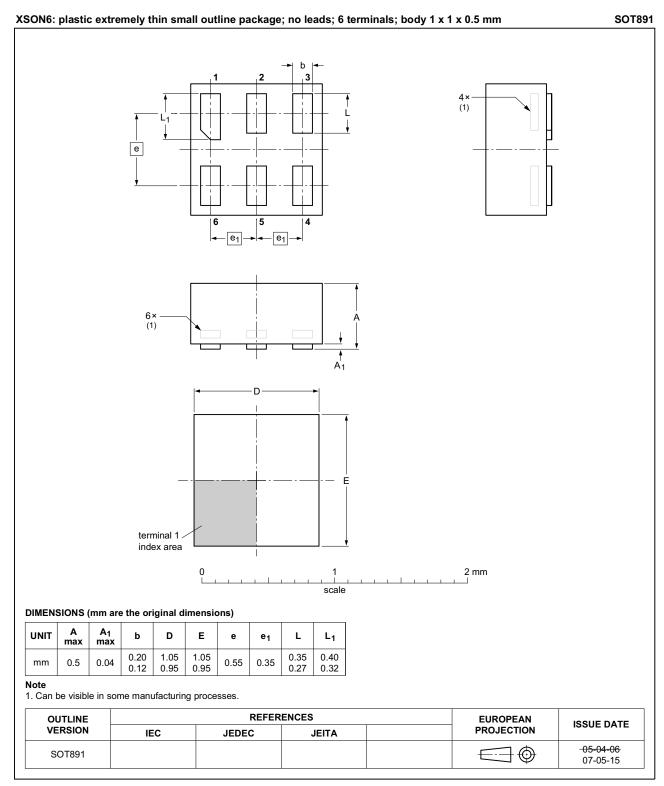


Fig 12. Package outline SOT891 (XSON6)

**Product data sheet** 

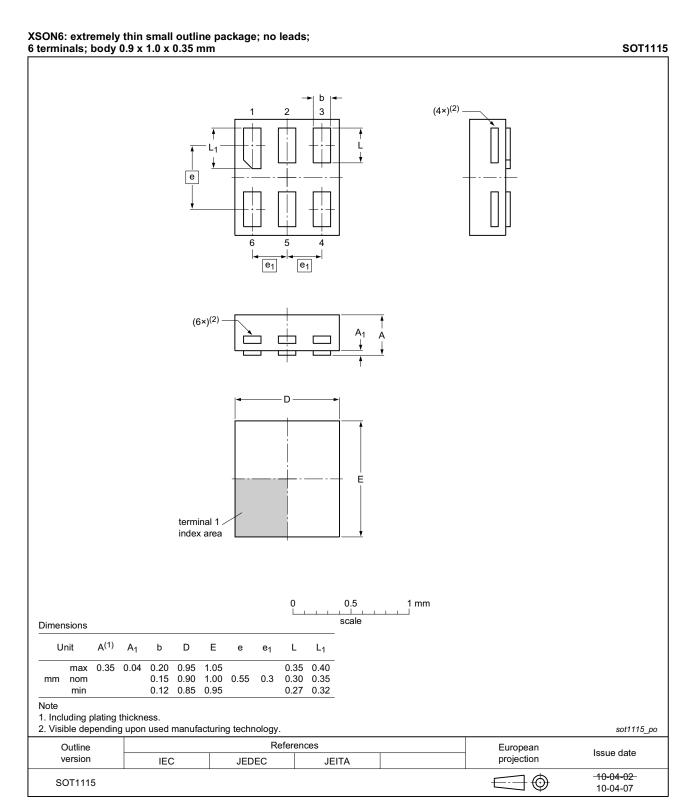


Fig 13. Package outline SOT1115 (XSON6)

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#### Low-power dual buffer with open-drain output

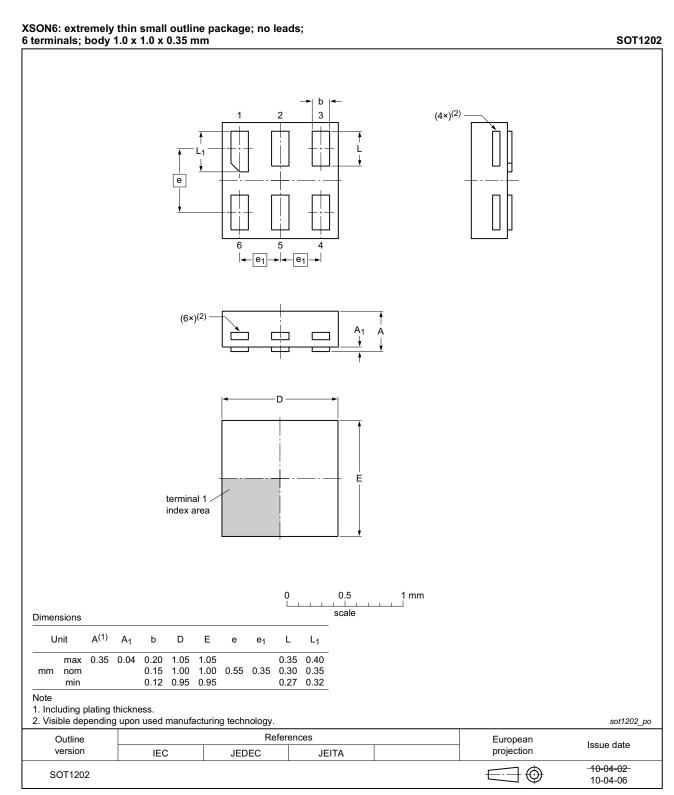


Fig 14. Package outline SOT1202 (XSON6)

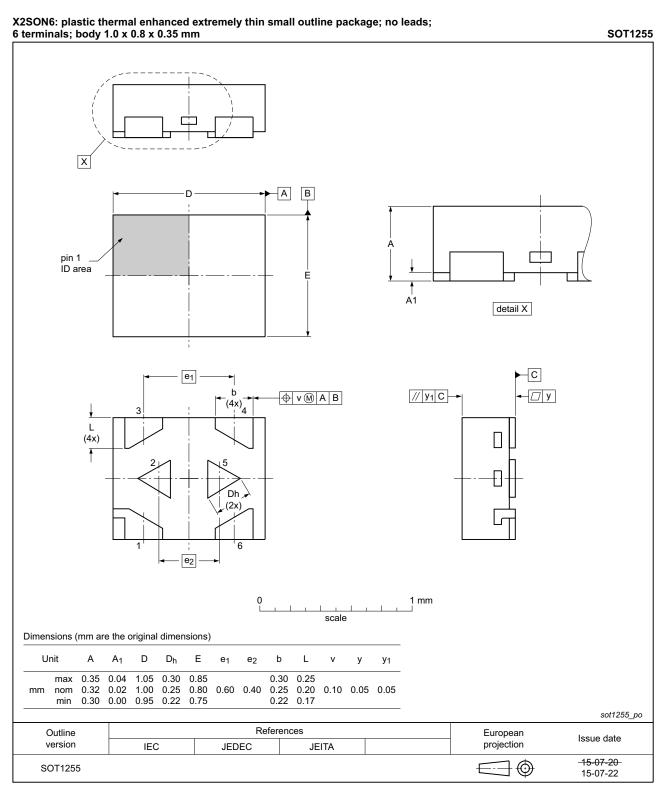


Fig 15. Package outline SOT1255 (X2SON6)

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### Low-power dual buffer with open-drain output

# 14. Abbreviations

#### Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

# 15. Revision history

#### Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP2G07 v.8	20150917	Product data sheet	-	74AUP2G07 v.7
Modifications:	Added type number 74AUP2G07GX (SOT1255/X2SON6).			
74AUP2G07 v.7	20121129	Product data sheet	-	74AUP2G07 v.6
Modifications:	Package outling	ne drawing of SOT886 (Figure	11) modified.	
74AUP2G07 v.6	20111202	Product data sheet	-	74AUP2G07 v.5
74AUP2G07 v.5	20100909	Product data sheet	-	74AUP2G07 v.4
74AUP2G07 v.4	20090611	Product data sheet	-	74AUP2G07 v.3
74AUP2G07 v.3	20071016	Product data sheet	-	74AUP2G07 v.2
74AUP2G07 v.2	20070612	Product data sheet	-	74AUP2G07 v.1
74AUP2G07 v.1	20061121	Product data sheet	-	-

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [1] Please consult the most recently issued document before initiating or completing a design.
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